Taiwan Semiconductor

# 3A, 200V-1000V Surface Mount Rectifier

## FEATURES

- Glass passivated junction chip
- Ideal for automated placement
- Low reverse leakage
- Moisture sensitivity level: level 1, per J-STD-020
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

## APPLICATIONS

- Switch Mode Power Supply
- Inverters and Converters
- Free Wheeling diodes

### **MECHANICAL DATA**

- Case: DO-214AA (SMB)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1 whisker test
- Polarity: Indicated by cathode band
- Weight: 0.09 g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I <sub>F</sub>	3	А	
V <sub>RRM</sub>	200-1000	V	
I <sub>FSM</sub>	80	А	
T <sub>J MAX</sub>	150	°C	
Package	DO-214AA	(SMB)	







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)							
PARAMETER	SYMBOL	S3DB-K	S3GB-K	S3JB-K	S3KB-K	S3MB-K	UNIT
Marking code on the device		S3DB	S3GB	S3JB	S3KB	S3MB	V
Repetitive peak reverse voltage	V <sub>RRM</sub>	200	400	600	800	1000	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	140	280	420	560	700	V
DC blocking voltage	V <sub>DC</sub>	200	400	600	800	1000	
Forward current	I <sub>F</sub>			3			А
Surge peak forward current single half sine- $8.3 \text{ ms at } T_A = 25^{\circ}$				80			А
wave superimposed on rated load per diode $1.0 \text{ ms at } T_A = 25^\circ$	I <sub>FSM</sub>			224			А
Junction temperature	TJ		-	55 to +15	0		°C
Storage temperature	T <sub>STG</sub>		-	55 to +15	0		°C





THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ТҮР	UNIT	
Junction-to-lead thermal resistance per diode	R <sub>ejl</sub>	20	°C/W	
Junction-to-ambient thermal resistance per diode	R <sub>eja</sub>	78	°C/W	
Junction-to-case thermal resistance per diode	R <sub>eJC</sub>	26	°C/W	

Thermal Performance Note: Units mounted on PCB(10mm x 10mm Cu pad test board)

ELECTRICAL SPECIFICATIONS ( $T_A = 25^{\circ}C$ unless otherwise noted)					
PARAMETER	CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Forward voltage per diode <sup>(1)</sup>	$I_F = 1.5A, T_J = 25^{\circ}C$	V <sub>F</sub>	0.88	-	V
	$I_F = 3A, T_J = 25^{\circ}C$		0.93	1.15	V
	I <sub>F</sub> = 1.5A, T <sub>J</sub> = 125°C		0.79	-	V
	$I_F = 3A, T_J = 125^{\circ}C$		0.87	0.99	V
Reverse current @ rated $V_R$ per diode $^{(2)}$	$T_J = 25^{\circ}C$	1	-	5	μA
	T <sub>J</sub> = 125°C	I <sub>R</sub>	-	300	μA
Junction capacitance per diode	1 MHz, V <sub>R</sub> =4.0V	CJ	60	-	pF

#### Notes:

(1) Pulse test with PW=0.3 ms

(2) Pulse test with PW=30 ms

ORDERING INFORMATION				
ORDERING CODE	PACKAGE	PACKING		
S3XB-K R5G <sup>(1)</sup>	SMB	850 / 7" Plastic reel		
S3XB-K M4G <sup>(1)</sup>	SMB	3,000 / 13" Plastic reel		
S3XB-K R4G <sup>(1)</sup>	SMB	3,000 / 13" Paper reel		

Notes:

(1) "X" defines voltage from 200V(S3DB-K) to 1000V(S3MB-K)



## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

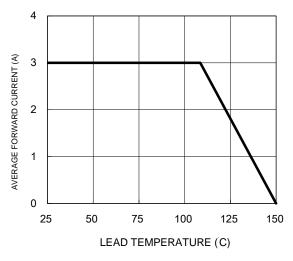
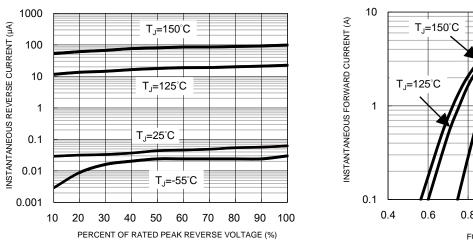
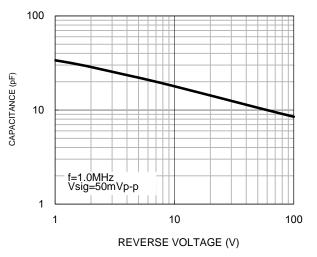


Fig.1 Forward Current Derating Curve

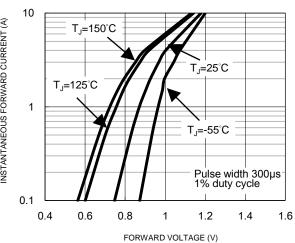
#### **Fig.3 Typical Reverse Characteristics**

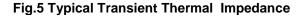


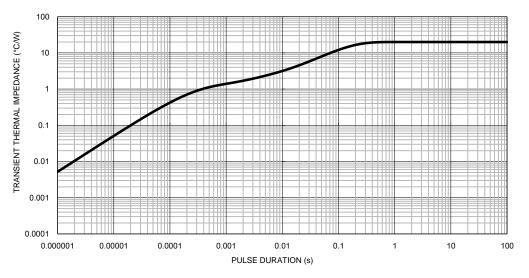


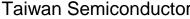
#### **Fig.2 Typical Junction Capacitance**

**Fig.4 Typical Forward Characteristics** 





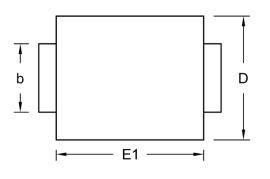


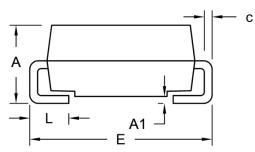




## **PACKAGE OUTLINE DIMENSIONS**

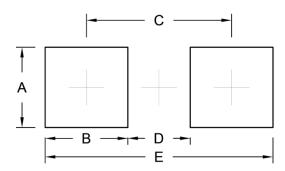
DO-214AA (SMB)





DIM.	Unit (mm)		Unit (	(inch)	
	Min.	Max.	Min.	Max.	
A	2.13	2.44	0.084	0.096	
A1	-	0.203	-	0.008	
b	1.80	2.20	0.071	0.087	
с	0.152	0.305	0.006	0.012	
D	3.30	3.94	0.130	0.155	
E	5.08	5.59	0.200	0.220	
E1	4.06	4.57	0.160	0.180	
L	0.76	1.52	0.030	0.060	

## SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	2.36	0.093
В	2.44	0.096
С	4.28	0.169
D	1.84	0.072
E	6.72	0.265

## **MARKING DIAGRAM**

P/N ⊈SYWF	

P/N	= Marking Code
G	= Green Compound
YW	= Date Code
F	= Factory Code



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